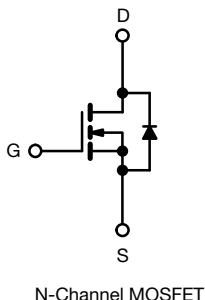
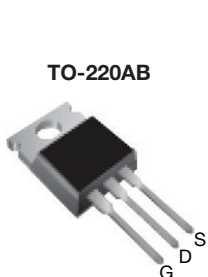


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	200	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.18
Q_g (Max.) (nC)	70	
Q_{gs} (nC)	13	
Q_{gd} (nC)	39	
Configuration	Single	



FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF640PbF
	SiHF640-E3
SnPb	IRF640
	SiHF640

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	200	V
Gate-Source Voltage			V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	18	A
		T _C = 100 °C		11	
Pulsed Drain Current ^a			I _{DM}	72	
Linear Derating Factor				1.0	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	580	mJ
Repetitive Avalanche Current ^a			I _{AR}	18	A
Repetitive Avalanche Energy ^a			E _{AR}	13	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	125	W
Peak Diode Recovery dV/dt ^c			dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) ^d	for 10 s			300	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

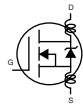

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 2.7\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 18\text{ A}$ (see fig. 12).
- $I_{SD} \leq 18\text{ A}$, $dI/dt \leq 150\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C , $I_D = 1\text{ mA}$	-	0.29	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 160\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ °C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 11\text{ A}^b$	-	-	0.18	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 11\text{ A}^b$	6.7	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	1300	-	pF
Output Capacitance	C_{oss}		-	430	-	
Reverse Transfer Capacitance	C_{rss}		-	130	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 18\text{ A}$, $V_{DS} = 160\text{ V}$, see fig. 6 and 13 ^b	-	-	70	nC
Gate-Source Charge	Q_{gs}		-	-	13	
Gate-Drain Charge	Q_{gd}		-	-	39	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$, $I_D = 18\text{ A}$, $R_g = 9.1\text{ }\Omega$, $R_D = 5.4\text{ }\Omega$, see fig. 10 ^b	-	14	-	ns
Rise Time	t_r		-	51	-	
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	
Fall Time	t_f		-	36	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	0.5	-	3.6	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	18	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	72	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ °C}$, $I_S = 18\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ °C}$, $I_F = 18\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	300	610	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	3.4	7.1	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

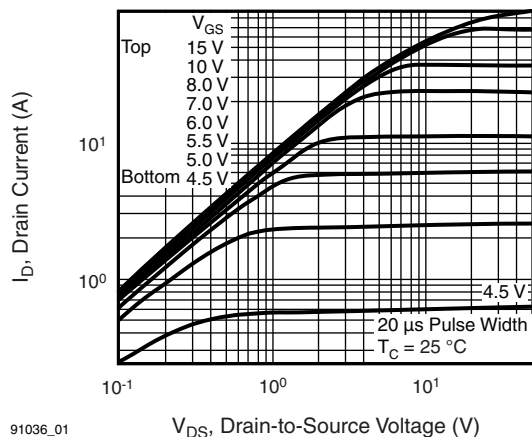


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ °C}$

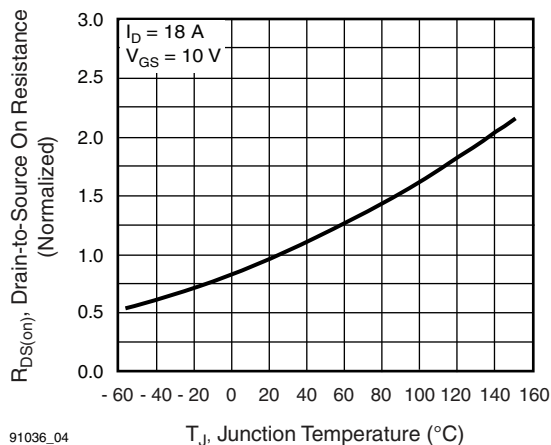


Fig. 4 - Normalized On-Resistance vs. Temperature

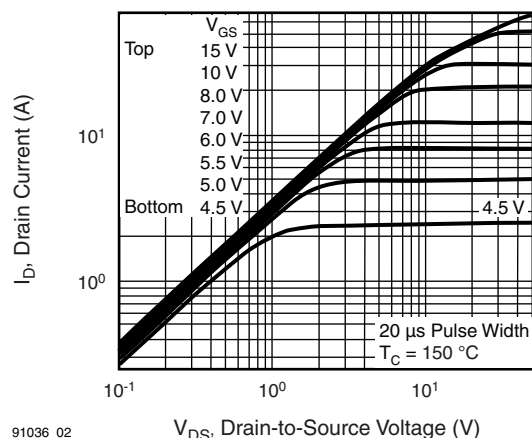


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ °C}$

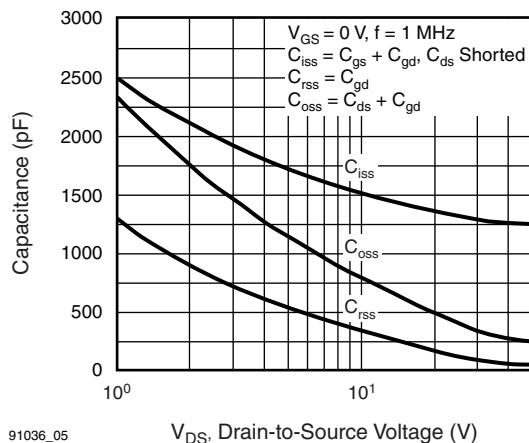


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

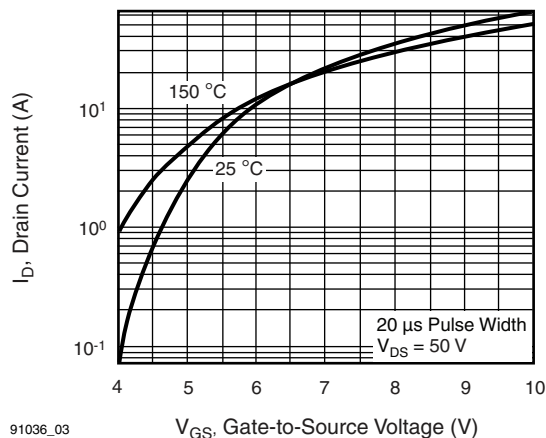


Fig. 3 - Typical Transfer Characteristics

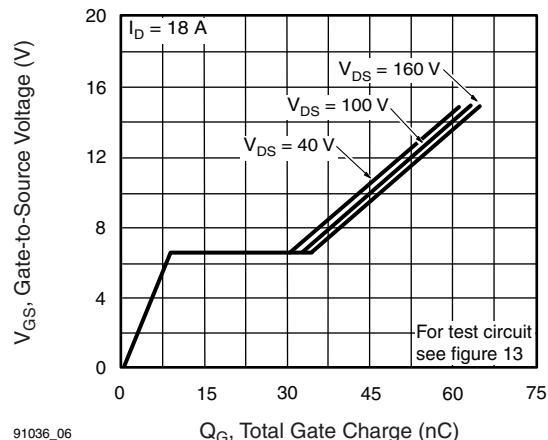
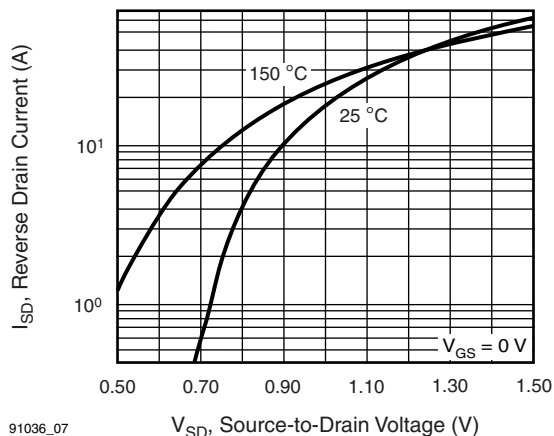
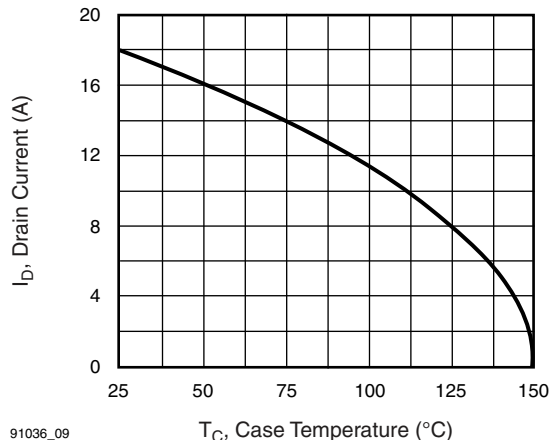
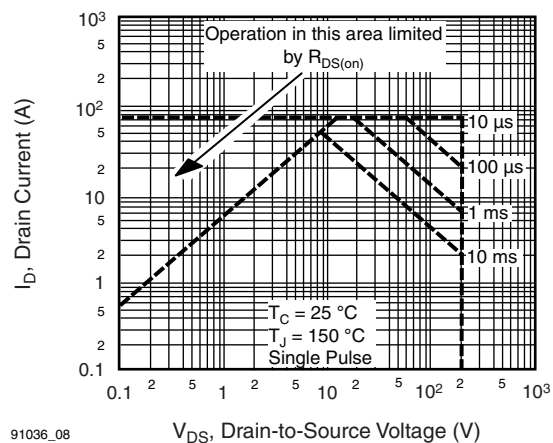
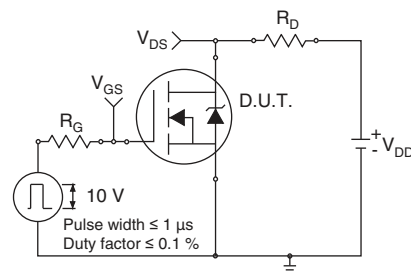
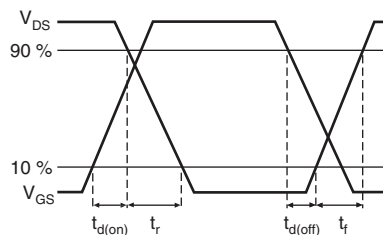
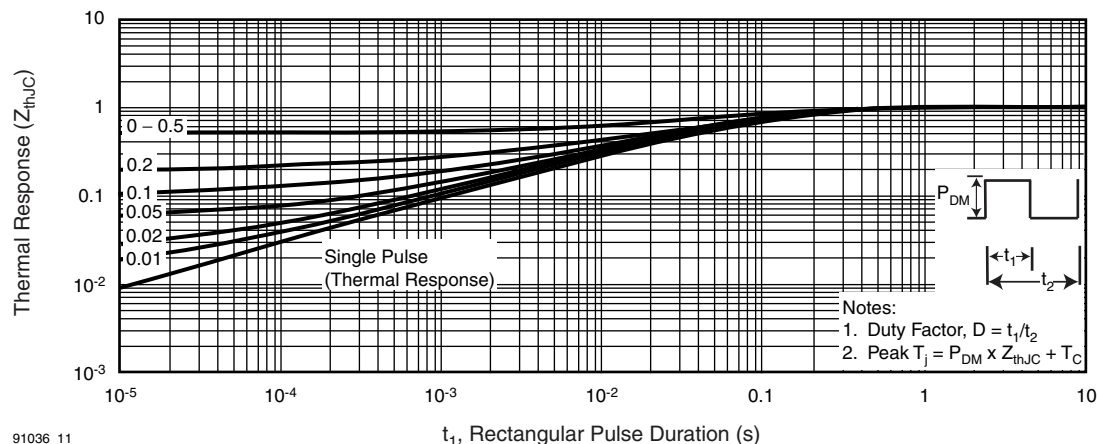
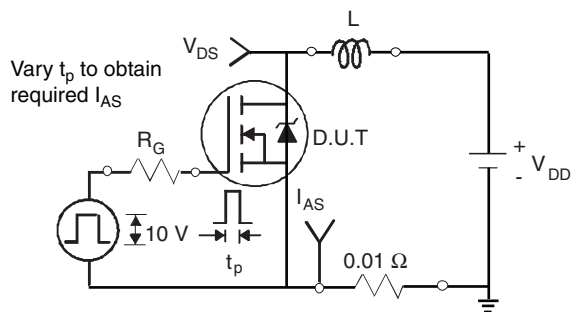
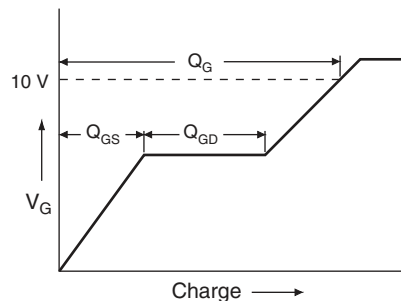
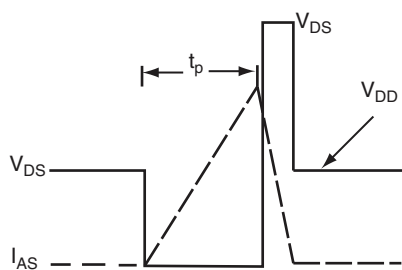
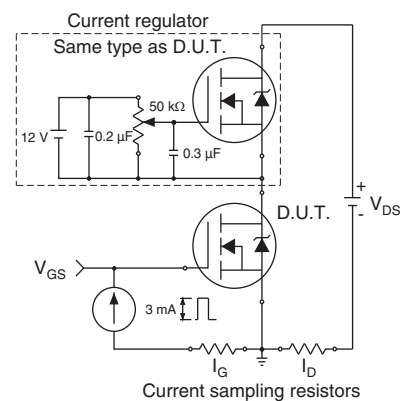
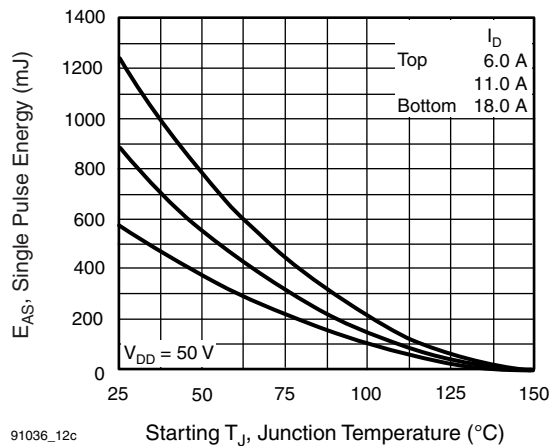


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

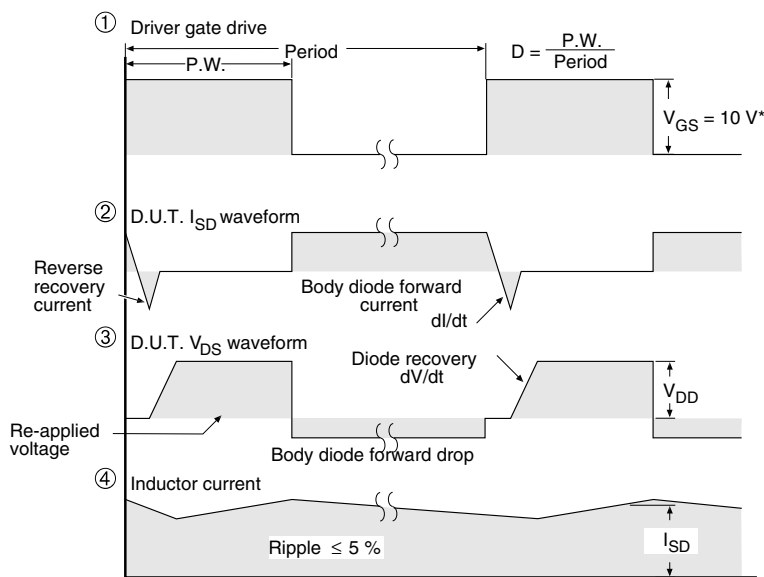
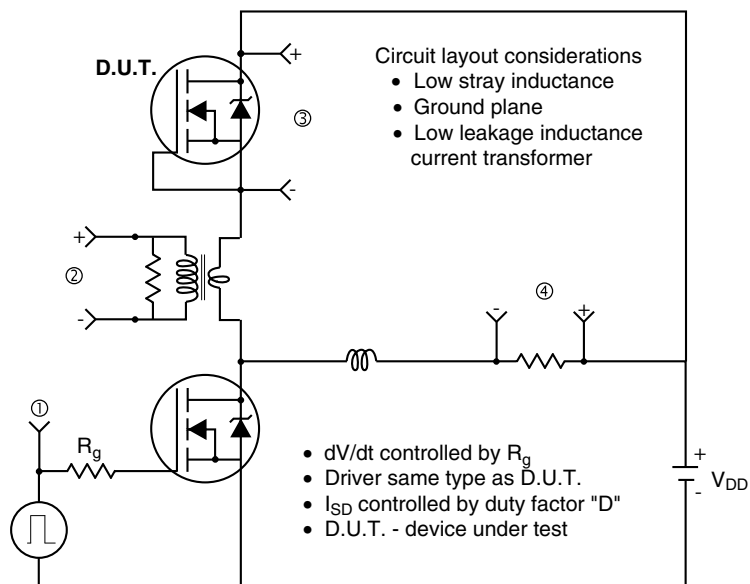

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 12a - Unclamped Inductive Test Circuit

Fig. 13a - Basic Gate Charge Waveform

Fig. 12b - Unclamped Inductive Waveforms

Fig. 13b - Gate Charge Test Circuit


91036_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91036>.

TO-220-1



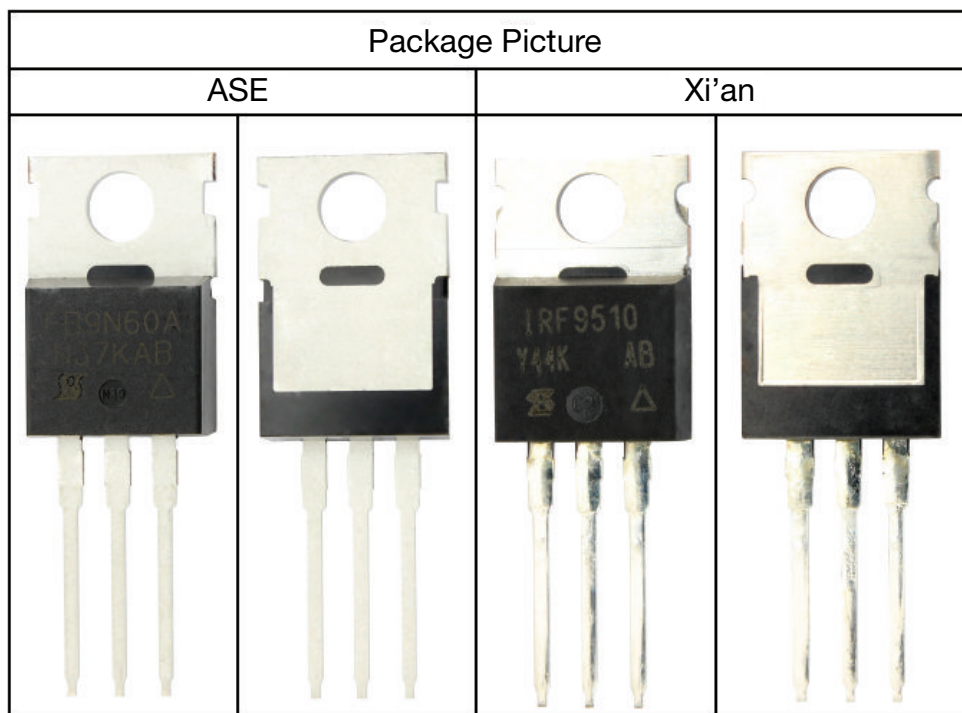
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	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

Package Picture





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